

STARPOWER

SEMICONDUCTOR

IGBT

GD300HTT120C7S_G8

1200V/300A 6 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverter and UPS.



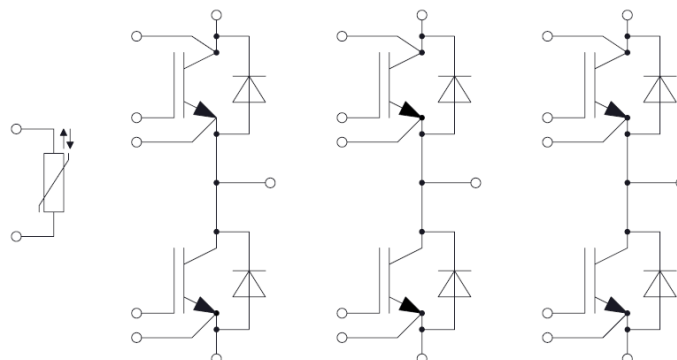
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 30	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	480	A
	@ $T_C=100^{\circ}\text{C}$	300	
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	600	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	1613	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	300	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	600	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	2500	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=300\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.70	2.15	V	
		$I_C=300\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		1.95			
		$I_C=300\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.00			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=12.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.0	5.6	6.5	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			5.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			0.7		Ω	
C_{ies}	Input Capacitance	$V_{CE}=30\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		29.7		nF	
C_{res}	Reverse Transfer Capacitance			0.90		nF	
Q_G	Gate Charge	$V_{GE}=15\text{V}$		1.80		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=300\text{A}, R_G=2.2\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		331		ns	
t_r	Rise Time			105		ns	
$t_{d(off)}$	Turn-Off Delay Time			521		ns	
t_f	Fall Time			124		ns	
E_{on}	Turn-On Switching Loss			6.30		mJ	
E_{off}	Turn-Off Switching Loss			27.3		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=600\text{V}, I_C=300\text{A}, R_G=2.2\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		327		ns
t_r	Rise Time				110		ns
$t_{d(off)}$	Turn-Off Delay Time			575		ns	
t_f	Fall Time			166		ns	
E_{on}	Turn-On Switching Loss			10.6		mJ	
E_{off}	Turn-Off Switching Loss			34.6		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=300\text{A}, R_G=2.2\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$			318		ns
t_r	Rise Time				111		ns
$t_{d(off)}$	Turn-Off Delay Time			586		ns	
t_f	Fall Time			185		ns	
E_{on}	Turn-On Switching Loss			11.5		mJ	
E_{off}	Turn-Off Switching Loss			37.0		mJ	
I_{SC}	SC Data		$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		1200		A

Diode Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=300\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.80	2.25	V
		$I_F=300\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.85		
		$I_F=300\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.85		
Q_r	Recovered Charge			29.3		μC
I_{RM}	Peak Reverse Recovery Current	$V_{CC}=600\text{V}, I_F=300\text{A},$ $-di/dt=2900\text{A}/\mu\text{s}, V_{GE}=-15\text{V},$ $T_j=25^\circ\text{C}$		236		A
E_{rec}	Reverse Recovery Energy			14.8		mJ
Q_r	Recovered Charge			52.8		μC
I_{RM}	Peak Reverse Recovery Current	$V_{CC}=600\text{V}, I_F=300\text{A},$ $-di/dt=2900\text{A}/\mu\text{s}, V_{GE}=-15\text{V},$ $T_j=125^\circ\text{C}$		302		A
E_{rec}	Reverse Recovery Energy			26.4		mJ
Q_r	Recovered Charge			60.8		μC
I_{RM}	Peak Reverse Recovery Current	$V_{CC}=600\text{V}, I_F=300\text{A},$ $-di/dt=2900\text{A}/\mu\text{s}, V_{GE}=-15\text{V},$ $T_j=150^\circ\text{C}$		322		A
E_{rec}	Reverse Recovery Energy			30.4		mJ

NTC Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of R_{100}	$T_c=100^\circ\text{C}, R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

Module Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		20		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		1.10		$\text{m}\Omega$
R_{thJC}	Junction-to-Case (per IGBT)			0.093	K/W
	Junction-to-Case (per Diode)			0.126	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.052		K/W
	Case-to-Heatsink (per Diode)		0.071		
	Case-to-Heatsink (per Module)		0.005		
M	Terminal Connection Torque, Screw M6	3.0		6.0	N.m
	Mounting Torque, Screw M5	3.0		6.0	
G	Weight of Module		910		g

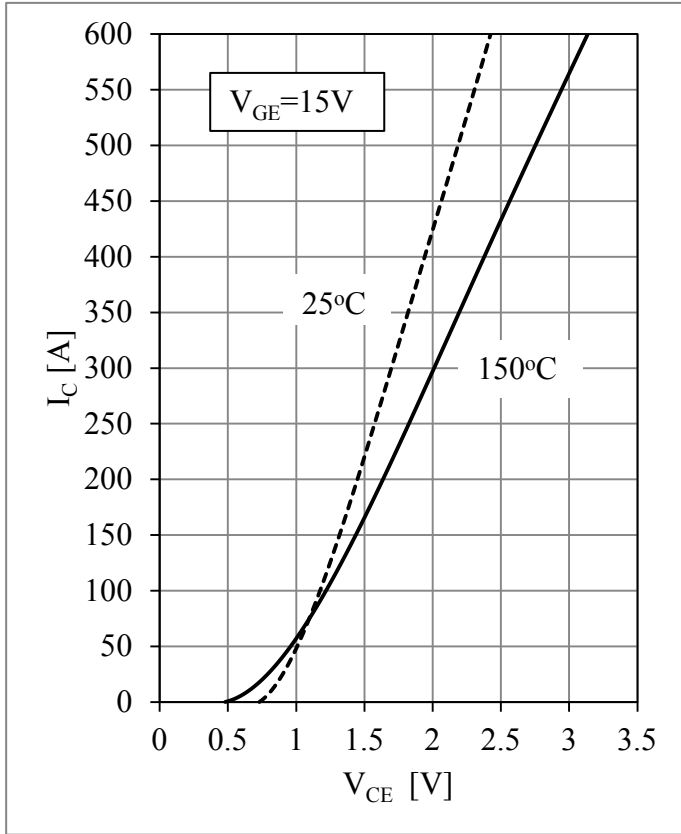


Fig 1. IGBT Output Characteristics

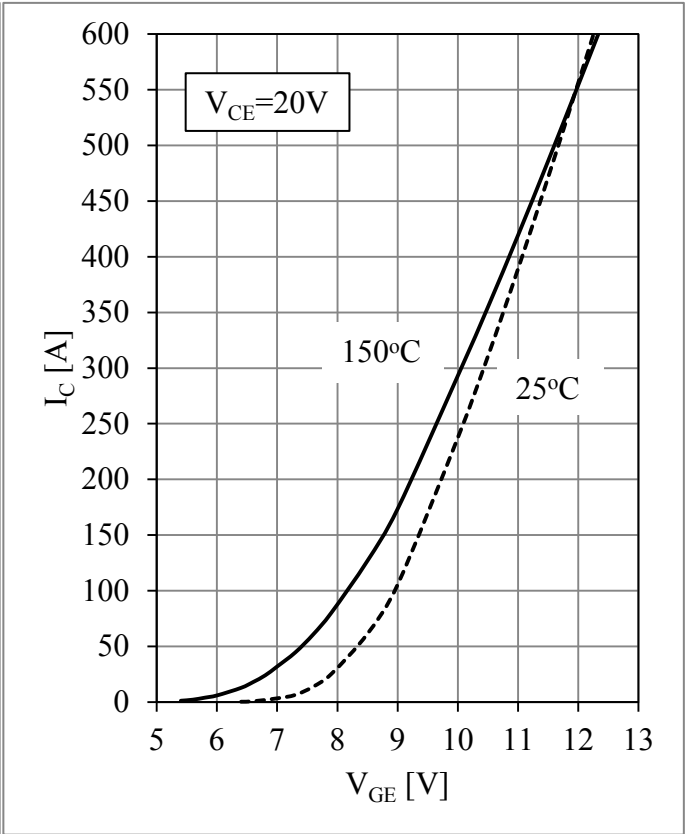


Fig 2. IGBT Transfer Characteristics

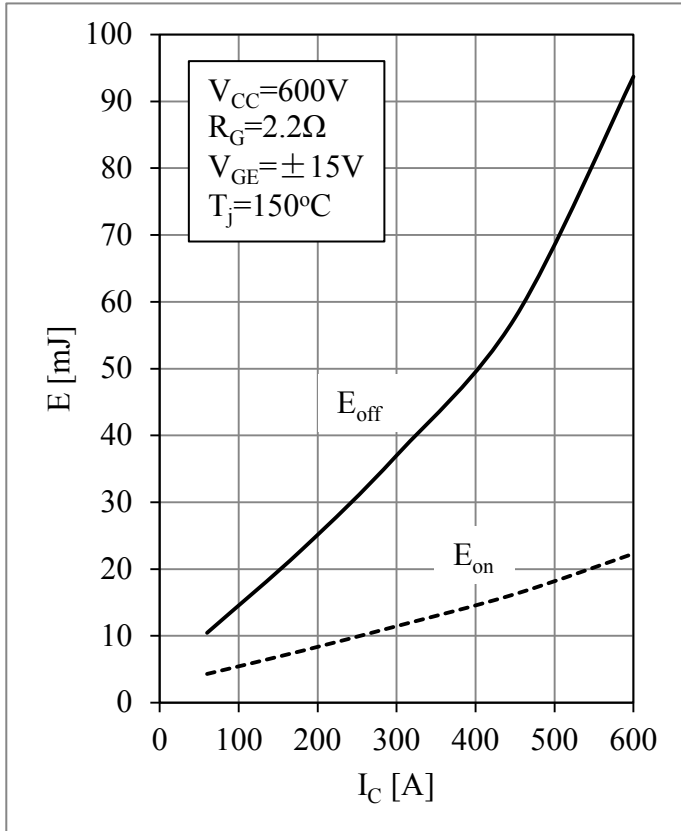


Fig 3. IGBT Switching Loss vs. I_C

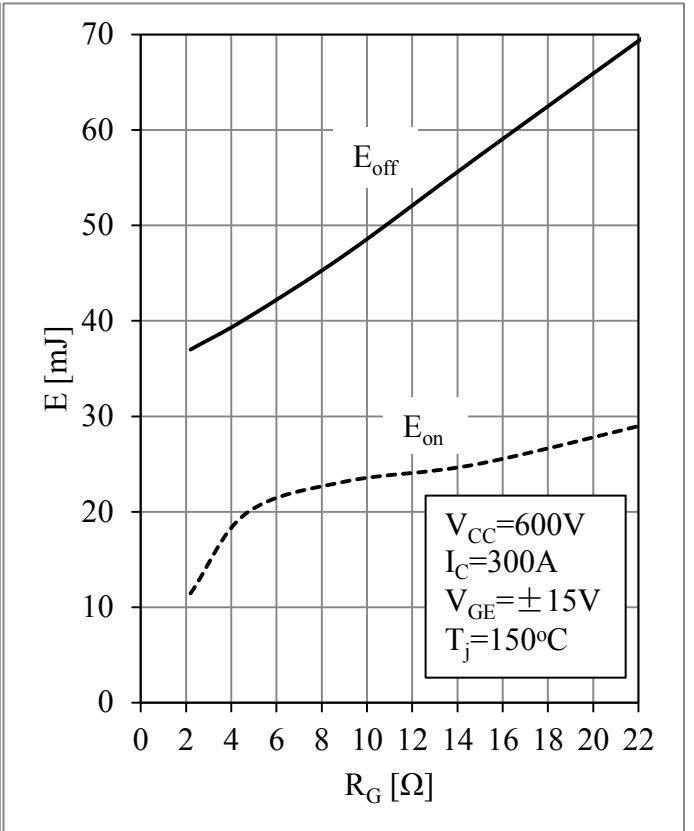


Fig 4. IGBT Switching Loss vs. R_G

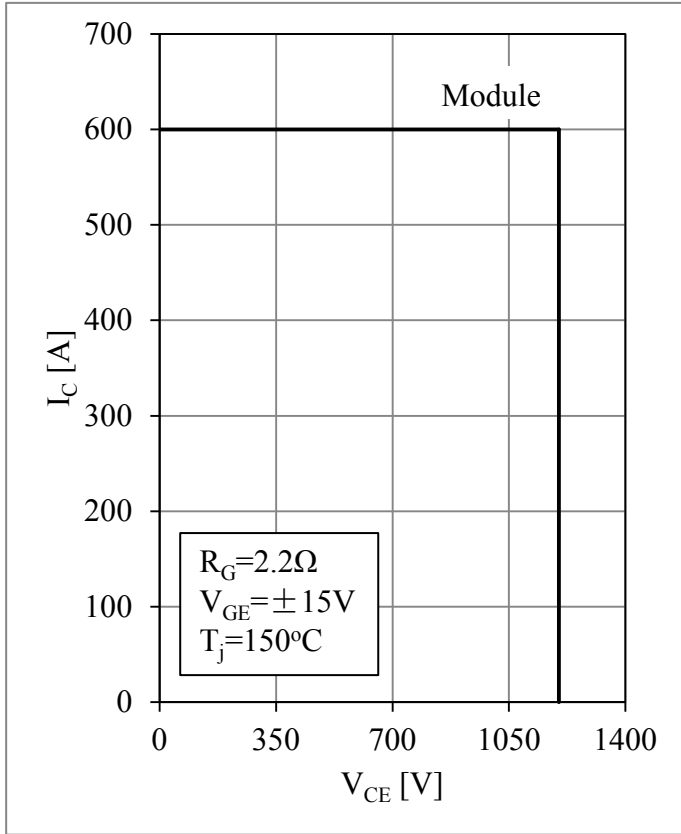


Fig 5. RBSOA

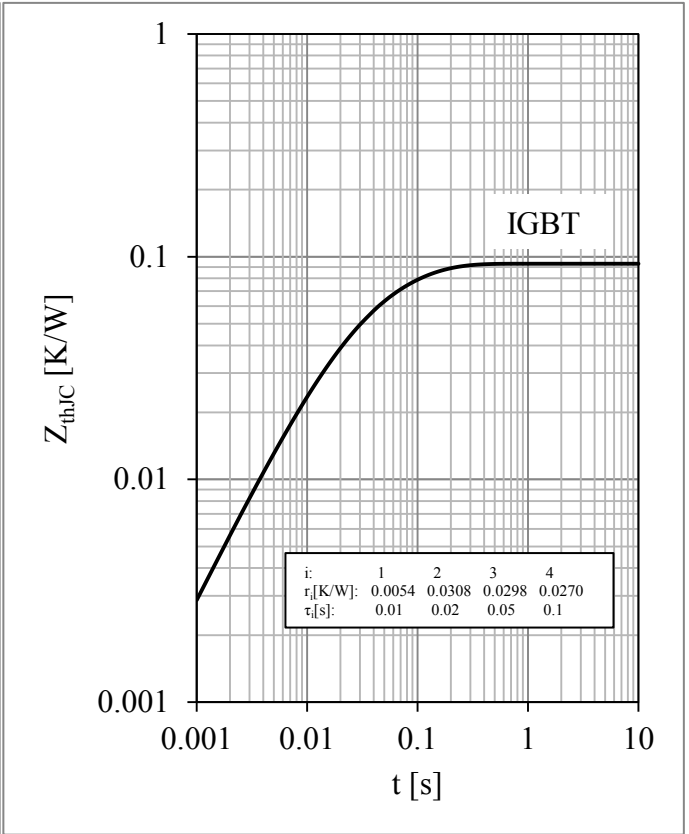


Fig 6. IGBT Transient Thermal Impedance

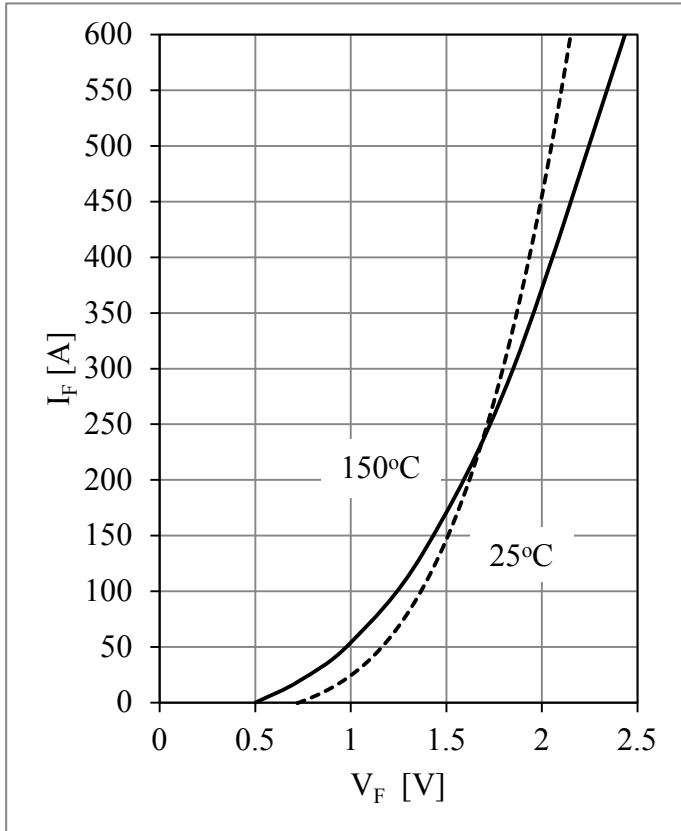


Fig 7. Diode Forward Characteristics

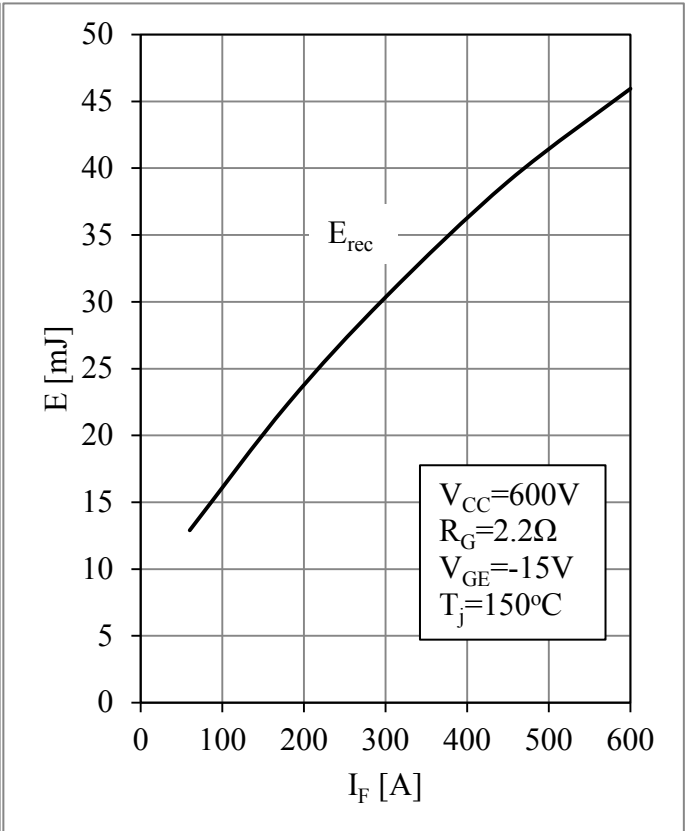


Fig 8. Diode Switching Loss vs. I_F

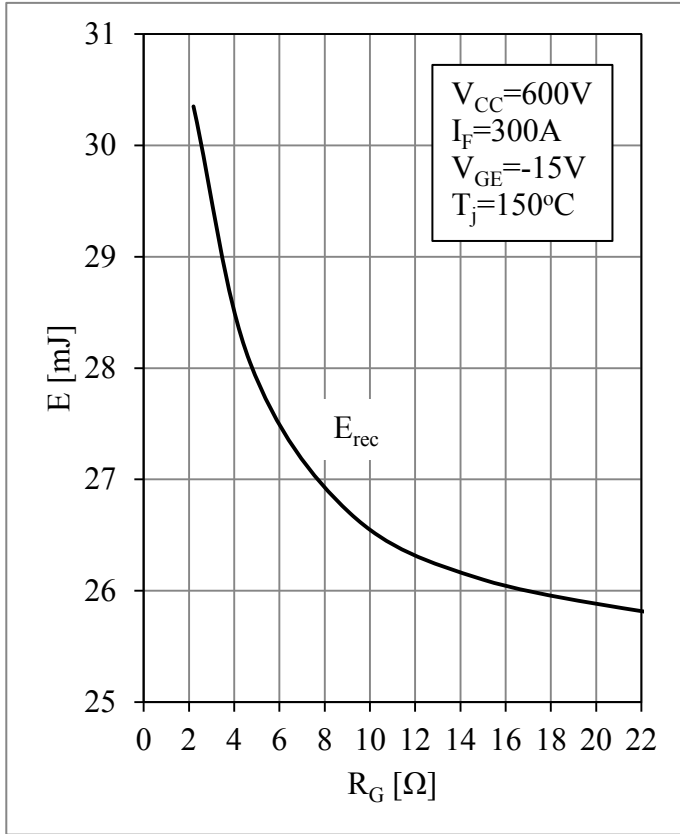


Fig 9. Diode Switching Loss vs. R_G

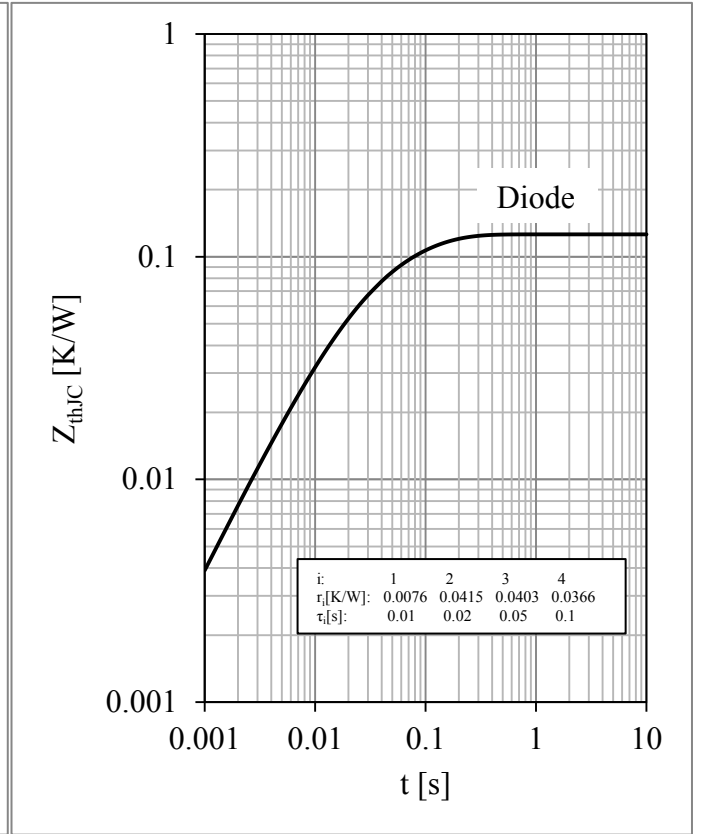


Fig 10. Diode Transient Thermal Impedance

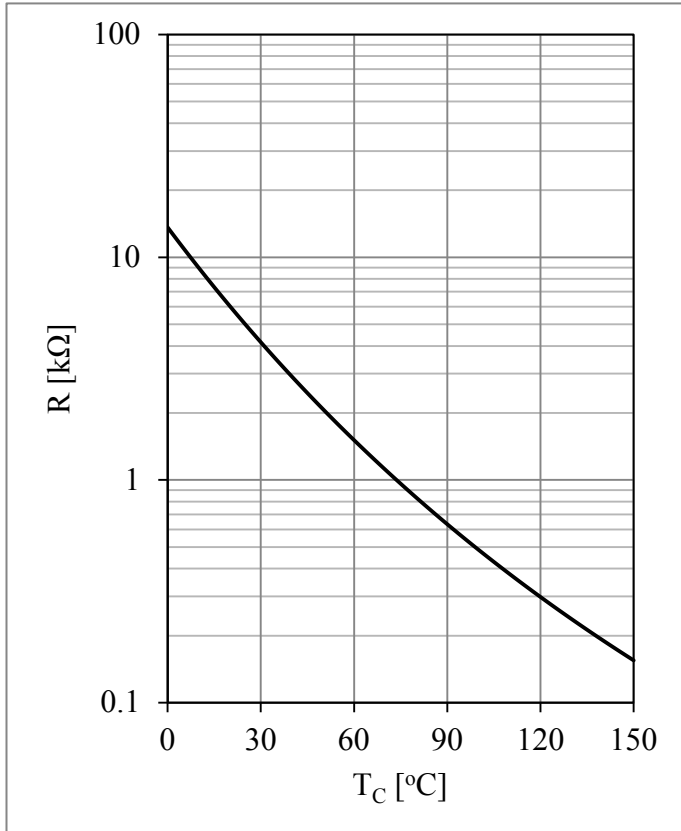
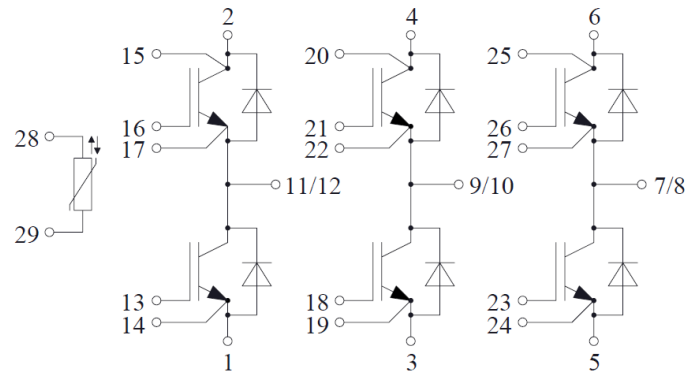


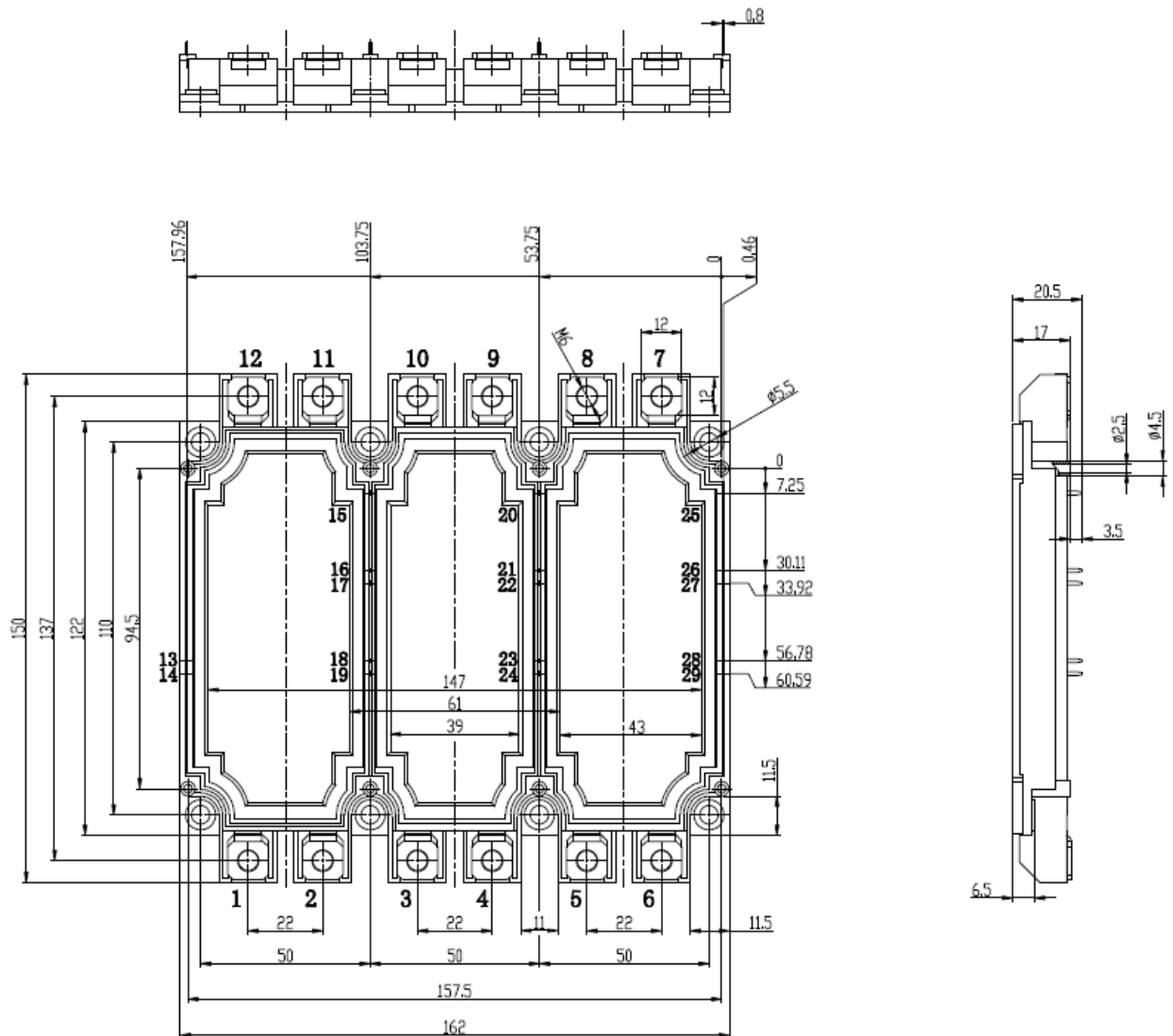
Fig 11. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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